



2DA1774QLP

#### 40V PNP SMALL SIGNAL TRANSISTOR IN DFN1006

### Features

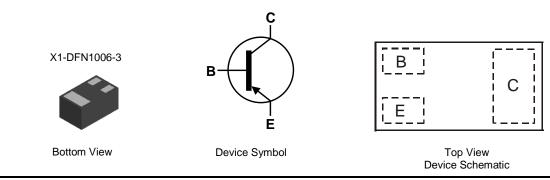
- BV<sub>CEO</sub> > -40V
- I<sub>C</sub> = -100mA High Collector Current
- P<sub>D</sub> = 1W Power Dissipation
- 0.6mm<sup>2</sup> Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type: 2DC4617QLP
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free, "Green" Device (Note 3)
- The 2DA1774QLP is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Package: X1-DFN1006-3

**Mechanical Data** 

- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu
  Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (Approximate)



# Ordering Information (Note 4)

Part Number	Package	Marking Code	Reel Size (inches)	Tape Width (mm)	Packing	
Fait Nulliber	Fackaye	Marking Code	Reel Size (Inches)	rape width (min)	Qty.	Carrier
2DA1774QLP-7	X1-DFN1006-3	8A	7	8	3,000	Reel
2DA1774QLP-7B	X1-DFN1006-3	8A	7	8	10,000	Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

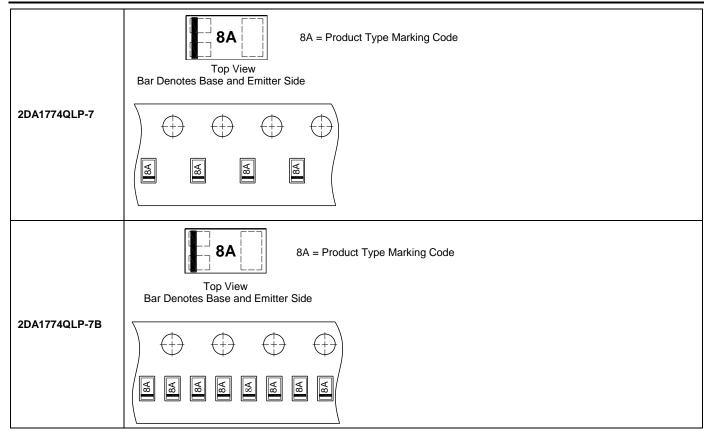
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**





### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	Vceo	-40	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current	lc	-100	mA
Peak Collector Current	Ісм	-200	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	0.4	W	
Power Dissipation	(Note 6)	PD	1		
Thermal Desistance, Junction to Ambient	(Note 5)	Reja	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)		120	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	R <sub>0JL</sub>	120	°C/W	
Operating and Storage and Temperature Ran	TJ, TSTG	-55 to +150	°C		

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

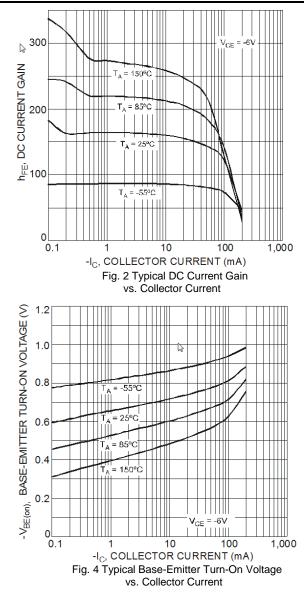
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)		•	•		·
Collector-Base Breakdown Voltage	ВУсво	-50		V	Ic = -50μA
Collector-Emitter Breakdown Voltage	BVCEO	-40		V	Ic = -1mA
Emitter-Base Breakdown Voltage	BVEBO	-5.0		V	I <sub>E</sub> = -50μA
Collector Cutoff Current	1	_	-100	nA	V <sub>CB</sub> = -30V
	Ісво		-5	μA	V <sub>CB</sub> = -30V, T <sub>A</sub> = +150°C
Emitter Cutoff Current	IEBO		-100	nA	$V_{EB} = -4V$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	hfe	120	270		$V_{CE} = -6V$ , $I_C = -1mA$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	-0.2	V	$I_{C} = -50 \text{mA}, I_{B} = -5 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Cobo		5.0	pF	$V_{CB} = -12V, f = 1MHz$
Current Gain-Bandwidth Product	fT	100		MHz	V <sub>CE</sub> = -12V, I <sub>C</sub> = -2mA, f = 100MHz

Notes: 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.
 Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



#### 100 I<sub>B</sub> = -0.5mA -l<sub>o</sub>, collector current (mA) I<sub>B</sub> = -0.4mA I<sub>B</sub> = -0.3mA $I_{B} = -0.2mA$ I<sub>B</sub> = -0.1mA 0 0 2 3 4 5 1 -V<sub>CE</sub>, COLLECTOR-EMITTER VOLTAGE (V) Fig. 1 Typical Collector Current vs. Collector-Emitter Voltage 0.5 -V<sub>CE(sat)</sub>, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 0.4 10 0.3 0.2 Т⊿ = 85°C 0.1 T<sub>A</sub> = 25°C -55⁰C 0 1 10 100 -I<sub>C</sub>, COLLECTOR CURRENT (mA) 0.1 1,000 Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current 1.2 1.0 -V<sub>BE(sat)</sub>, BASE-EMITTER SATURATION VOLTAGE (V) 0.8 -55°C 25°C 0.6 85°C 0.4 11|| 150°0 0.2 10 /I<sub>B</sub> 0 0.1 10 100 1,000 -I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

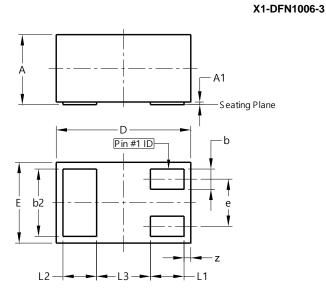


### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



### **Package Outline Dimensions**

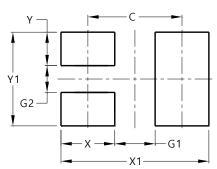
Please see http://www.diodes.com/package-outlines.html for the latest version.



Х	X1-DFN1006-3					
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.075	1.00			
Е	0.55	0.675	0.60			
е	-	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
z	0.02	0.08	0.05			
All D	All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



### X1-DFN1006-3

Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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